

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	"6297539".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:20
L3	1	"6015739".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:20
L4	1	"6013553".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:21
L5	1	"4335391".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:23
L6	1	"4151537".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:23
L7	765	@ad<="20020322" and (257/310). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 10:28
L8	2080	@ad<="20020322" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 10:29
S1	2	"20030178674"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:50
S2	1985	@ad<="20020322" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 10:02
S3	143	@ad<="20020322" and (438/216). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:50
S4	318	@ad<="20020322" and (438/261). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 10:57
S5	713	@ad<="20020322" and (438/287). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 10:58
S6	844	@ad<="20020322" and (438/585). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:00

S7	448	@ad<="20020322" and (438/587-588).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:00
S8	317	@ad<="20020322" and (438/591).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:04
S9	298	@ad<="20020322" and (438/791).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:04
S10	196	@ad<="20020322" and (438/792).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:05
S11	50	@ad<="20020322" and 'MOS' same 'high dielectric' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:10
S12	9	@ad<="20020322" and 'MOS' same 'Hafnium oxide' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:38
S13	196	@ad<="20020322" and 'MOS' same 'aluminum oxide' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:06
S14	16	@ad<="20020322" and 'high dielectric' same 'aluminum oxide' same 'nitride layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:33
S15	3	@ad<="20020322" and 'MOS' same 'high dielectric constant' same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 16:02
S16	302	@ad<="20020322" and 'high dielectric constant' and 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 07:55
S17	14	@ad<="20020322" and 'high dielectric constant' and 'plasma nitriding'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:09

S18	2	"20020137317"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:23
S19	2	("6482694").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/12/30 12:24
S20	2	("6339246").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/12/30 12:24
S21	24	bai-gang.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:51
S22	50	@ad<="20020322" and 'nitridation' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:05
S23	5	@ad<="20020322" and 'plasmas' adj1 'nitridation' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 07:56
S24	3	@ad<="20020322" and 'plasmas' adj1 'nitriding' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 07:56
S25	5	@ad<="20020322" and 'plasma nitridation' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:15
S26	162	@ad<="20020322" and 'nitride layer' with 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:33
S27	128	@ad<="20020322" and 'nitride layer' with 'tantalum oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:49
S28	76	@ad<="20020322" and 'polysilicon' same 'tantalum oxide' same 'nitride layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:32

S29	46	@ad<="20020322" and 'nitride layer' with 'high k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 09:36
S30	102	@ad<="20020322" and 'p-type polysilicon gate' same 'n-type polysilicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 10:33
S31	140	@ad<="20020322" and 'p-type polysilicon' with 'boron'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 10:35
S32	35	@ad<="20020322" and 'p-type polysilicon gate' with 'boron'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 10:36
S33	1	"6291868".PN.	USPAT	OR	OFF	2003/12/31 10:42
S34	2	("6436848").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/29 13:29
S35	36	@ad<="20020322" and 'nitridation' same 'high k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:05
S36	415	@ad<="20020322" and "'HfO.sub.2'" same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:40
S37	175	@ad<="20020322" and "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:26
S38	19	@ad<="20020322" and 'high k' same "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:40
S39	43	@ad<="20020322" and 'high k' and "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:41
S40	54	@ad<="20020322" and 'high dielectric' and "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:09

S41	2	"20010053601"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:04
S42	3	@ad<="20020322" and 'MIS' and 'high dielectric' and "'HfO.sub.2'" same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:10
S43	2	"20020089023"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:27
S44	10	@ad<="20020322" and "'Al.sub.2O. sub.3'" same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:02
S45	5	@ad<="20020322" and "'HfO.sub. 2'" same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 14:57
S46	12	@ad<="20020322" and "'ZrO.sub. 2'" same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 14:58
S47	13	@ad<="20020322" and "'Al.sub.2O. sub.3'" with 'nitride' adj1 'layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:03
S48	180	@ad<="20020322" and "'HfO.sub. 2'" with "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:26
S49	42	@ad<="20020322" and 'MOS' and "'HfO.sub.2'" with "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:39
S50	128	@ad<="20020322" and 'MOS' and 'high k' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:39
S51	741	@ad<="20020322" and (257/310). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 10:28

S52	551	@ad<="20020322" and (257/410). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 10:29
S53	531	@ad<="20020322" and (257/411). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:33
S54	957	@ad<="20020322" and (257/412). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:33
S55	411	@ad<="20020322" and (257/413). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:33
S56	153	@ad<="20020322" and (438/216). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:51
S57	855	@ad<="20020322" and (438/240). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:51
S58	24	@ad<="20020322" and 'MOS' same 'high dielectric' with 'gate' same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 16:12
S59	21	@ad<="20020322" and 'MOS' same 'gate' with 'high k' same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 16:13
S60	2067	@ad<="20020322" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 10:02